



Schottky Diodes



- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 ℃

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

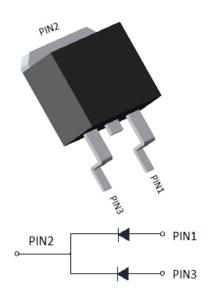
Mechanical Data

• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant

 Terminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102

Polarity: As marked



■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRBL20100CT
Device marking code			MBRBL20100CT
Repetitive Peak Reverse Voltage	VRRM	V	100
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25℃	Ю	Α	20
Surge(Non-repetitive)Forward Current @60H _Z half sine-wave, 1 cycle, T _a =25°C	IFSM	Α	150
Current Squared Time @1ms≤t<8.3ms Tj=25℃	l ² t	A ² s	94
Storage Temperature	T _{stg}	$^{\circ}$	-55 ~ +1 50
Junction Temperature	Tj	$^{\circ}$	-55 ~ +150

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRBL20100CT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=10.0A	0.72
Maximum DC reverse current	IRRM1	mA	VRM=VRRM T _a =25°C	0.1
at rated DC blocking voltage per diode	IRRM2		VRM=VRRM T _a =100°C	20

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS

MBRBL20100CT

PARAMETER		SYMBOL	UNIT	MBRBL20100CT
Thermal Resistance	Between junction and case	R _{θJ-C}	°CMV	2.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBRBL20100CT	Approximate 1.43	50	2000	8000	Tube
MBRBL20100CT	Approximate 1.43	1000	2000	10000	Reel

■Characteristics (Typical)

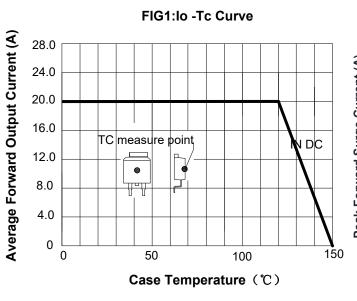
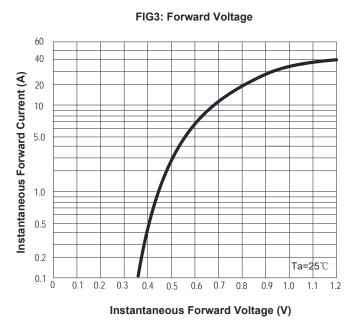
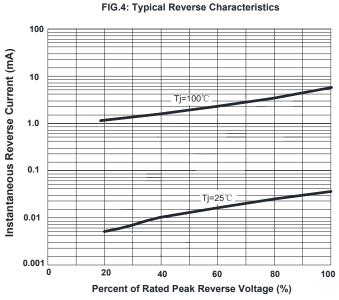


FIG2:Surge Forward Current Capability 175 Peak Forward Surge Current (A) 150 125 8.3ms Single Half Sine-Wave 100 JEDEC Method 75 50 25 2 5 20 50 100 10

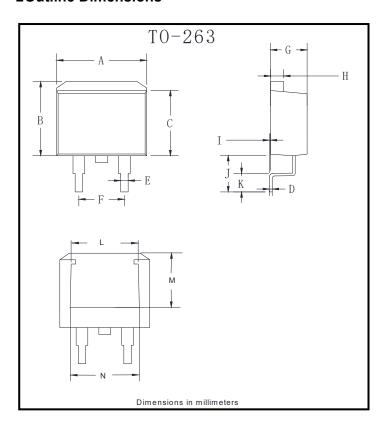
Number of Cycles





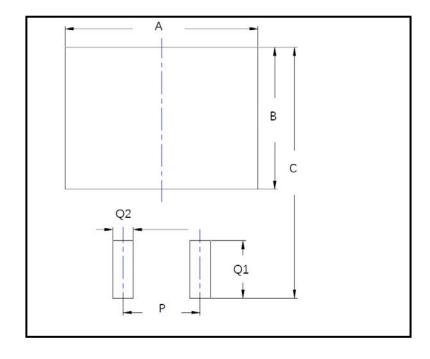


■Outline Dimensions



TO-263				
Dim	Min	Max		
Α	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
Е	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
1	0	0.2		
J	4.9	6.05		
K	1.79	2.79		
L	7.3	7.9		
М	6.2	6.8		
N	7.6	8.2		

■Suggested Pad Layout



Dim	Millimeters		
Α	12.7		
В	9.4		
С	16.6		
Р	5.08		
Q1	3.8		
Q2	1.35		



MBRBL20100CT

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